

ISSUE CLASSIFICATION	
Class	Subclass

FILED UNDER 35 U.S.C. 371:

PATENT NUMBER

U.S. UTILITY Patent Application

O.I.P.E.

PATENT DATE

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SCANNED KS3 Q.A. 103

APPLICATION NO. 09/856209	CONT/PRIOR D F	CLASS 117	SUBCLASS B3	ART UNIT 1765	EXAMINER Atedh
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Silicon single crystal and production method for silicon single crystal wafer

TITLE	APPLICANTS
1. Administrative	
2. Business	
3. Education	
4. Health	
5. Law	
6. Science	
7. Social Sciences	
8. Arts and Humanities	
9. Other	

ISSUING CLASSIFICATION

[illegible]

<input type="checkbox"/> TERMINAL DISCLAIMER	DRAWINGS		CLAIMS ALLOWED	
	Sheets Drwg.	Figs. Drwg.	Print Fig.	Total Claims
<input type="checkbox"/> The term of this patent subsequent to _____ (date) has been disclaimed.	_____ (Assistant Examiner) (Date)		NOTICE OF ALLOWANCE MAILED	
	<input type="checkbox"/> The term of this patent shall not extend beyond the expiration date of U.S Patent. No. _____ _____ _____		ISSUE FEE	
Amount Due			Date Paid	
<input type="checkbox"/> The terminal ____ months of this patent have been disclaimed.	_____ (Legal Instruments Examiner) (Date)		ISSUE BATCH NUMBER	
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